

BRMJD32CQ

Rev.A Apr.-2024

/ Descriptions

KF \$,) GE G Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

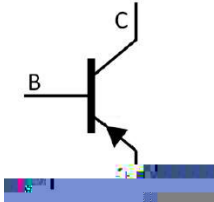
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Low Speed ,Load Formed for Surface Mount Application, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

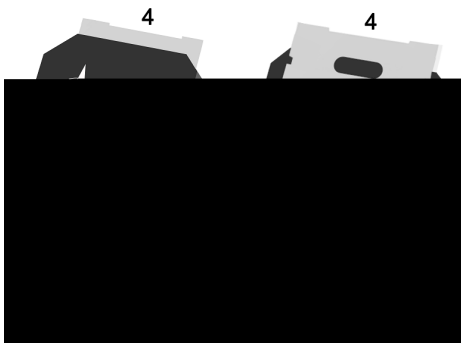
/ Applications

General Purpose Amplifier, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



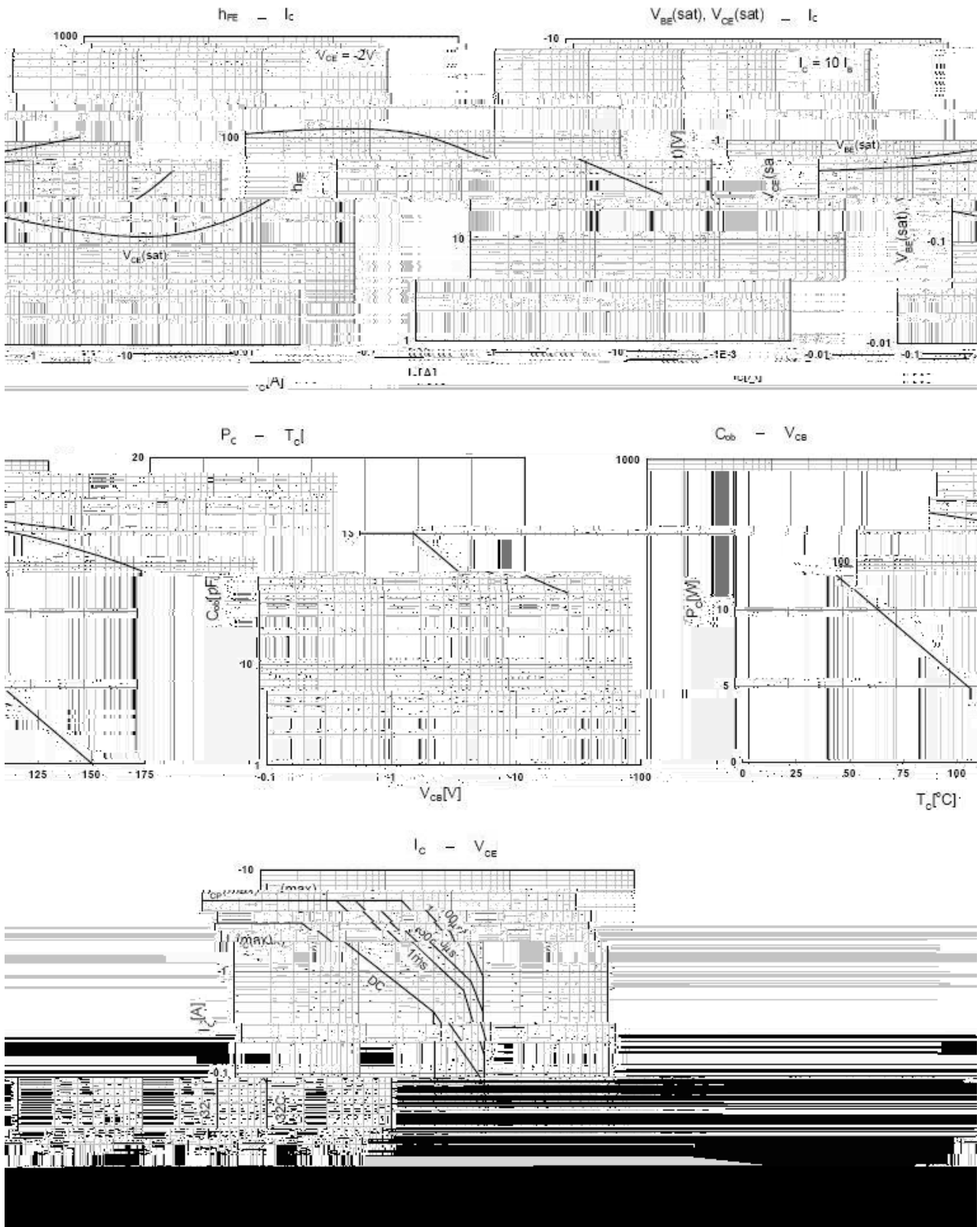
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ hFE Classifications & Marking

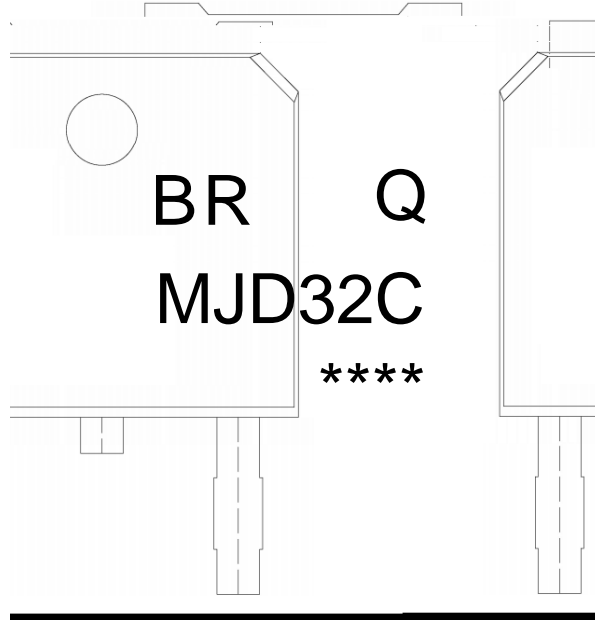
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V

/ Electrical Characteristic Curve



/ Marking Instructions



BR

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Note:

BR: Company Code

Q: Automobile halogen-free product Code

MJD32C: Product Type

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1 150 200 60 120sec; 1.Preheating:150~200 , Time:60~120sec.
- 2 255..5 5..0.5sec; 2.Peak Temp.:255..5 , Duration:5..0.5sec.
- 3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.